

SLAS222B - APRIL 1999-REVISED NOVEMBER 2010

16 D BUSL1

15 🖽 GND

14 🖽 RIS

13 🖽 RXI

12 🞞 RX

11 🞞 VDD

10 🗔 VS

9 🖽 BAT

D PACKAGE (TOP VIEW)

BUSL2 III 1

STC III 3

RIDD I 4

PF 🖂 5

SC III 6

TX 🖂 8

# **METER-BUS TRANSCEIVER**

Check for Samples: TSS721A

### FEATURES

•	Meter-Bus Transceiver (for Slave) Meets
	Standard EN1434-3

- Receiver Logic With Dynamic Level Recognition
- Adjustable Constant-Current Sink via Resistor
- Polarity Independent
- Power-Fail Function
- Module Supply Voltage Switch
- 3.3-V Constant Voltage Source
- Remote Powering
- Up to 9600 Baud in Half Duplex for UART Protocol
- Slave Power Support
  - Supply From Meter-Bus via Output VDD
  - Supply From Meter-Bus via Output VDD or From Backup Battery
  - Supply From Battery Meter-Bus Active for Data Transmission Only

### DESCRIPTION

TSS721A is a single chip transceiver developed for Meter-Bus standard (EN1434-3) applications.

The TSS721A interface circuit adjusts the different potentials between a slave system and the Meter- Bus master. The connection to the bus is polarity independent and supports full galvanic slave isolation with optocouplers.

The circuit is supplied by the master via the bus. Therefore, this circuit offers no additional load for the slave battery. A power-fail function is integrated.

The receiver has dynamic level recognition, and the transmitter has a programmable current sink.

A 3.3-V voltage regulator, with power reserve for a delayed switch off at bus fault, is integrated.

#### Table 1. ORDERING INFORMATION<sup>(1)(2)</sup>

T <sub>A</sub>	PACI	KAGE	ORDERABLE PART NUMBER
0°C to 70°C	SOIC – D	Reel of 2500	TSS721ADR

(1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.

(2) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.



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Figure 1.	Functional	Schematic
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|--|

TERMI	NAL						
NAME	NO.	ifferential bus voltage after rectifier upport capacitor current adjustment input ower fail output ampling capacitor rata output inverted rata output ogic level adjust					
BUSL2	1	Meter-Bus					
VB	2	Differential bus voltage after rectifier					
STC	3	Support capacitor					
RIDD	4	Current adjustment input					
PF	5	Power fail output					
SC	6	Sampling capacitor					
ТХІ	7	Data output inverted					
ТХ	8	Data output					
BAT	9	Logic level adjust					
VS	10	Switch for bus or battery supply output					
VDD	11	Voltage regulator output					
RX	12	Data input					
RXI	13	Data input inverted					
RIS	14	Adjust input for modulation current					
GND	15	Ground					
BUSL1	16	Meter-Bus					



#### Data Transmission, Master to Slave

The mark level on the bus lines  $V_{BUS}$  = MARK is defined by the difference of BUSL1 and BUSL2 at the slave. It is dependent on the distance of Master to Slave, which affects the voltage drop on the wire. To make the receiver independent, a dynamic reference level on the SC pin is used for the voltage comparator TC3 (see Figure 2).



Figure 2. Data Transmission, Master to Slave

A capacitor C<sub>SC</sub> at pin SC is charged by a current I<sub>SCcharge</sub> and is discharged with a current I<sub>SCdischarge</sub> where:

$$I_{\text{SCdisharge}} = \frac{I_{\text{SCcharge}}}{40 \text{ (typ)}} \tag{1}$$

This ratio is necessary to run any kind of UART protocol independent of the data contents. (for example, if an 11-bit UART protocol is transmitted with all data bits at 0 and only the stop bit at 1). There must be sufficient time to recharge the capacitor  $C_{SC}$ . The input level detector TC3 detects voltage modulations from the master,  $V_{BUS} = SPACE/MARK$  conditions, and switches the inverted output TXI and the non-inverted output TX.

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Data Transmission, Slave to Master

The device uses current modulation to transmit information from the slave to the master while the bus voltage remains constant. The current source CS3 modulates the bus current and the master detects the modulation. The constant current source CS3 is controlled by the inverted input RXI or the non-inverted input RX. The current source CS3 can be programmed by an external resistor  $R_{RIS}$ . The modulation supply current  $I_{MS}$  flows in addition to the current source CS3 during the modulation time.



Figure 3. Data Transmission, Slave to Master

Because the TSS721A is configured for half-duplex only, the current modulation from RX or RXI is repeated concurrently as ECHO on the outputs TX and TXI. If the slave, as well as the master, is trying to send information via the lines, the added signals appear on the outputs TX and TXI, which indicates the data collision to the slave (see Figure 1).

The bus topology requires a constant current consumption by each connected slave.

To calculate the value of the programming resistor R<sub>RIS</sub>, use the formula shown in Figure 4.



Figure 4. Calculate Programming Resistor R<sub>RIS</sub>



(2)

### Slave Supply, 3.3 V

The TSS721A has an internal 3.3-V voltage regulator. The output power of this voltage regulator is supplied by the storage capacitor  $C_{STC}$  at pin STC. The storage capacitor  $C_{STC}$  at pin STC is charged with constant current  $I_{STC\_use}$  from the current source CS1. The maximum capacitor voltage is limited to REF1. The charge current  $I_{STC}$  has to be defined by an external resistor at pin RIDD.

The adjustment resistor  $R_{RIDD}$  can be calculated using Equation 2.

$$R_{\text{RID}} = 25 \frac{V_{\text{RIDD}}}{I_{\text{STC}}} = 25 \frac{V_{\text{RIDD}}}{I_{\text{STC}_{\text{use}}} + I_{\text{IC1}}}$$

Where,

 $I_{STC}$  = current from current source CS1

 $I_{STC use}$  = charge current for support capacitor

 $I_{CI}$  = internal current

 $V_{RIDD}$  = voltage on pin RIDD

R<sub>RIDD</sub> = value of adjustment resistor

The voltage level of the storage capacitor  $C_{STC}$  is monitored with comparator TC1. Once the voltage  $V_{STC}$  reaches  $V_{VDD\_on}$ , the switch  $S_{VDD}$  connects the stabilized voltage  $V_{VDD}$  to pin VDD. VDD is turned off if the voltage  $V_{STC}$  drops below the  $V_{VDD\_off}$  level.

Voltage variations on the capacitor  $C_{STC}$  create bus current changes (see Figure 5).



At a bus fault the shut down time of VDD ( $t_{off}$ ) in which data storage can be performed depends on the system current  $I_{VDD}$  and the value of capacitor  $C_{STC}$ . See Figure 6, which shows a correlation between the shutdown of the bus voltage  $V_{BUS}$  and  $V_{DD}$  off and  $t_{off}$  for dimensioning the capacitor.

The output VS is meant for slave systems that are driven by the bus energy, as well as from a battery should the bus line voltage fail. The switching of VS is synchronized with VDD and is controlled by the comparator TC1. An external transistor at the output VS allows switching from the Meter-Bus remote supply to battery.

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### Power On/Off



Figure 6. Power On/Off Timing

### **Power Fail Function**

Because of the rectifier bridge BR at the input, BUSL1, and BUSL2, the TSS721A is polarity independent. The pin VB to ground (GND) delivers the bus voltage  $V_{VB}$  less the voltage drop over the rectifier BR. The voltage comparator TC2 monitors the bus voltage. If the voltage  $V_{VB} > V_{STC} + 0.6$  V, then the output PF = 1. The output level PF = 0 (power fail) provides a warning of a critical voltage drop to the microcontroller to save the data immediately.

#### **ABSOLUTE MAXIMUM RATINGS**

over operating free-air temperature range (unless otherwise noted)

$V_{MB}$	Voltage, BUSL1 to BUSL2		±50 V
		RX and RXI	–0.3 V to 5.5 V
vı	Input voltage range	BAT	–0.3 V to 5.5 V
TJ	Operating junction temperature range		–25°C to 150°C
T <sub>A</sub>	Operating free-air temperature range		–25°C to 85°C
T <sub>STG</sub>	Storage temperature range		-65°C to 150°C
	Power derating factor, junction to ambient		8 mW/°C

### **RECOMMENDED OPERATING CONDITIONS**<sup>(1)</sup>

			MIN	MAX	UNIT
V <sub>MB</sub>		Receiver	10.8	42	V
	Bus voltage,  BUSL2 – BUSL1	Transmitter	12	42	v
V	logut voltage	VB (receive mode)	9.3		v
VI	Input voltage	BAT <sup>(2)</sup>	2.5	3.8	v
R <sub>RIDD</sub>	RIDD resistor		13	80	kΩ
R <sub>RIS</sub>	RIS resistor		100		Ω
T <sub>A</sub>	Operating free-air temperature		-25	85	°C

(1) All voltage values are measured with respect to the GND terminal unless otherwise noted.

(2)  $V_{BAT}(max) \le V_{STC} - 1 V$ 

# ELECTRICAL CHARACTERISTICS<sup>(1)</sup>

over operating free-air temperature range (unless otherwise noted)

	PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$\Delta V_{BR}$	Voltage drop at rectifier BR	I <sub>BUS</sub> = 3 mA				1.5	V
$\Delta V_{CS1}$	Voltage drop at current source CS1	R <sub>RIDD</sub> = 13 kΩ				1.8	V
I <sub>BUS</sub>	BUS current	$V_{STC} = 6.5 V,$ $I_{MC} = 0 mA$	$R_{RIDD} = 13 kΩ$ $R_{RIDD} = 30 kΩ$			3 1.5	mA
ΔI <sub>BUS</sub>	BUS current accuracy	$\Delta V_{BUS} = 10 V,$	$M_{MC} = 0 \text{ mA}, \text{ R}_{RIDD} = 13 \text{ k}\Omega \text{ to } 30 \text{ k}\Omega$			2	%
I <sub>CC</sub>	Supply current	$V_{STC} = 6.5 \text{ V}, I_N$	$_{MC}$ = 0 mA, V <sub>BAT</sub> = 3.8 V, R <sub>RIDD</sub> = 13 k $\Omega^{(2)}$			650	μA
I <sub>CI1</sub>	CI1 current	$V_{STC} = 6.5 \text{ V}, \text{ I}_{\text{N}}$ $V_{\text{BUS}} = 6.5 \text{ V}, \text{ R}$	$_{MC}$ = 0 mA, V <sub>BAT</sub> = 3.8 V, R <sub>RIDD</sub> = 13 k $\Omega$ , X/RXI = off $^{(2)}$			350	μA
I <sub>BAT</sub>	BAT current			-0.5		0.5	μA
$I_{BAT} + I_{VDD}$	BAT plus VDD current	$V_{BUS} = 0 V, V_{S}$	TC = 0 V	-0.5		0.5	μA
V <sub>VDD</sub>	VDD voltage	$-I_{VDD} = 1 \text{ mA}, \text{V}$	/ <sub>STC</sub> = 6.5 V	3.1		3.4	V
$R_{VDD}$	VDD resistance	$-I_{VDD} = 2 \text{ to } 8 \text{ m}$	nA, V <sub>STC</sub> = 4.5 V			5	Ω
		$V_{DD}$ = on, VS =	on	5.6		6.4	
V <sub>STC</sub>	STC voltage	$V_{DD} = off, VS =$	off	3.8		4.3	V
		I <sub>VDD</sub> < I <sub>STC_use</sub>		6.5		7.5	
	070		$R_{RIDD} = 30 \text{ k}\Omega$	0.65		1.1	0
I <sub>STC_use</sub>	STC current	$V_{STC} = 5 V$	$R_{RIDD} = 13 \text{ k}\Omega$	1.85		2.4	mA
V <sub>RIDD</sub>	RIDD voltage	$R_{RIDD} = 30 \ k\Omega$		1.23		1.33	V
V <sub>VS</sub>	VS voltage	$V_{DD}$ = on, $I_{VS}$ =	5 μΑ	$V_{STC} - 0.4$		V <sub>STC</sub>	V
R <sub>VS</sub>	VS resistance	$V_{DD} = off$		0.3		1	MΩ
			$V_{VB} = V_{STC} + 0.8 \text{ V}, I_{PF} = -100 \mu\text{A}$	V <sub>BAT</sub> - 0.6		$V_{BAT}$	
V <sub>PF</sub>	PF voltage	$V_{STC}$ = 6.5 V	$V_{VB} = V_{STC} + 0.3 \text{ V}, I_{PF} = 1 \ \mu\text{A}$	0		0.6	V
			$V_{VB} = V_{STC} + 0.3 \text{ V}, I_{PF} = 5 \ \mu\text{A}$	0		0.9	

(1) All voltage values are measured with respect to the GND terminal, unless otherwise noted.

(2) Inputs RX/RXI and outputs TX/TXI are open,  $I_{CC} = I_{C11} + I_{C12}$ 

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## ELECTRICAL CHARACTERISTICS<sup>(1)</sup> (continued)

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t <sub>on</sub>	Turn-on time	$C_{STC}$ = 50 µF, Bus voltage slew rate: 1 V/µs			3	S

## **RECEIVER SECTION ELECTRICAL CHARACTERISTICS**<sup>(1)</sup>

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP MAX	UNIT
V <sub>T</sub>		See Figure 2	MARK - 8.2	MARK – 5.7	V
V <sub>SC</sub>	SC voltage			V <sub>VB</sub>	V
I <sub>SCcharge</sub>	SC charge current	$V_{SC} = 24 \text{ V}, V_{VB} = 36 \text{ V}$	-15	-40	μA
I <sub>SCdischarge</sub>	SC discharge current	$V_{SC} = V_{VB} = 24 V$	0.3	−0.033 × I <sub>SCcharge</sub>	μA
V <sub>OH</sub>	High-level output voltage (TX, TXI)	$I_{TX}/I_{TXI} = -100 \ \mu A$ (see Figure 2)	V <sub>BAT</sub> – 0.6	V <sub>BAT</sub>	V
V	Low-level output voltage	I <sub>TX</sub> /I <sub>TXI</sub> = 100 μA	0	0.5	V
V <sub>OL</sub>	(TX, TXI)	I <sub>TX</sub> = 1.1 mA	0	1.5	
I <sub>TX</sub> I <sub>TXI</sub>	TX, TXI current	$V_{TX} = 7.5, V_{VB} = 12 V, V_{STC} = 6 V, V_{BAT} = 3.8 V$		10	μA

(1) All voltage values are measured with respect to the GND terminal, unless otherwise noted.

### TRANSMITTER SECTION ELECTRICAL CHARACTERISTICS<sup>(1)</sup>

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	ΤΥΡ ΜΑΧ	UNIT	
I <sub>MC</sub>	MC voltage	R <sub>RIS</sub> = 100 Ω	11.5	19.5	mA	
V <sub>IH</sub> I	DIS voltogo	R <sub>RIS</sub> = 100 Ω	1.4	1.7	v	
	RIS voltage	R <sub>RIS</sub> = 1000 Ω	1.5	1.8		
V <sub>IH</sub>	High-level input voltage (RX, RXI)	See Figure 3, see <sup>(2)</sup>	V <sub>BAT</sub> – 0.8	5.5	V	
V <sub>IL</sub>	Low-level input voltage (RX, RXI)	See Figure 3	0	0.8	V	
	DV sument	$V_{RX} = V_{BAT} = 3 V, V_{VB} = V_{STC} = 0 V$	-0.5	0.5		
I <sub>RX</sub>	RX current	$V_{RX} = 0 V, V_{BAT} = 3 V, V_{STC} = 6.5 V$	-10	-40	μA	
	DVI ourrent	$V_{RXI} = V_{BAT} = 3 V, V_{VB} = V_{STC} = 0 V$	10	40		
I <sub>RXI</sub>	RXI current	$V_{RXI} = V_{BAT} = 3 \text{ V},  V_{STC} = 6.5 \text{ V}$	10	40	μA	

(1) All voltage values are measured with respect to the GND terminal, unless otherwise noted.

(2)  $V_{IH}(max) = 5.5 \text{ V}$  is valid only when  $V_{STC} > = 6.5 \text{ V}$ .



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### **APPLICATION INFORMATION**



NOTE: Transistor T1 should be a BSS84.

Figure 7. Basic Application Circuit Using Support Capacitor  $C_{STC} > 50 \ \mu F$ 



 $S_{sc}$  - support capacitor  $C_{sc}$  - sampling capacitor  $C_{voo}$  - stabilising capacitor (100 nF)  $C_{src}$ :  $C_{voo} >= 4:1$ 

Figure 8. Basic Application Circuit for Supply From Battery

 $R_{load}$  - discharge resistor (100 k $\Omega$  recommended)

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NOTE: R<sub>DSon</sub> of the transistor T1 (BSS84) at low battery voltage must be considered during application design.

Figure 9. Basic Applications for Different Supply Modes



Figure 10. Basic Optocoupler Application



### PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TSS721AD	ACTIVE	SOIC	D	16	40	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	TSS721A	Samples
TSS721ADR	ACTIVE	SOIC	D	16	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	TSS721A	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

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<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

<sup>(5)</sup> Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

<sup>(6)</sup> Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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# PACKAGE OPTION ADDENDUM

10-May-2022



5-Jan-2022

## TUBE



#### \*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	Τ (μm)	B (mm)
TSS721AD	D	SOIC	16	40	505.46	6.76	3810	4

D (R-PDSO-G16)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AC.



4211283-4/E 08/12

# D (R-PDSO-G16) PLASTIC SMALL OUTLINE Stencil Openings (Note D) Example Board Layout (Note C) –16x0,55 -14x1,27 -14x1,27 16x1,50 5,40 5.40 Example Non Soldermask Defined Pad Example Pad Geometry (See Note C) 0,60 .55 Example 1. Solder Mask Opening (See Note E) -0,07 All Around

NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
  E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



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